## EC2725ETTTS-66.666M



- Nominal Frequency

66.666MHz

L Pin 1 Connection

Duty Cycle 50 ±5(%)

Tri-State (High Impedance)

Series -RoHS Compliant (Pb-free) 2.5V 4 Pad 5x7mm Ceramic SMD LVCMOS Oscillator

Frequency Tolerance/Stability ±25ppm Maximum

Operating Temperature Range --40°C to +85°C

#### **ELECTRICAL SPECIFICATIONS**

Nominal Frequency	66.666MHz	
Frequency Tolerance/Stability	±25ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at 25°C, Shock, and Vibration)	
Aging at 25°C	±5ppm/year Maximum	
Operating Temperature Range	-40°C to +85°C	
Supply Voltage	2.5Vdc ±5%	
Input Current	10mA Maximum	
Output Voltage Logic High (Voh)	90% of Vdd Minimum (IOH = -4mA)	
Output Voltage Logic Low (Vol)	10% of Vdd Maximum (IOL = +4mA)	
Rise/Fall Time	3nSec Maximum (Measured at 20% to 80% of waveform)	
Duty Cycle	50 ±5(%) (Measured at 50% of waveform)	
Load Drive Capability	15pF Maximum	
Output Logic Type	CMOS	
Pin 1 Connection	Tri-State (High Impedance)	
Tri-State Input Voltage (Vih and Vil)	90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)	
Standby Current	10µA Maximum (Disabled Output, High Impedance)	
RMS Phase Jitter	1pSec Maximum (12kHz to 20MHz offset frequency)	
Start Up Time	10mSec Maximum	
Storage Temperature Range	-55°C to +125°C	

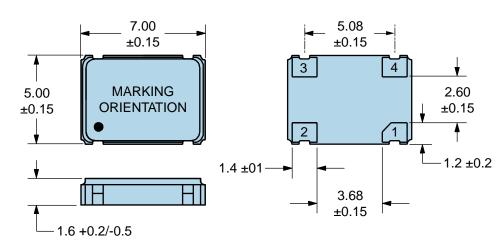
EC27 25 ET T TS -66.666M

### **ENVIRONMENTAL & MECHANICAL SPECIFICATIONS**

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V	
Fine Leak Test	MIL-STD-883, Method 1014, Condition A	
Flammability	UL94-V0	
Gross Leak Test	MIL-STD-883, Method 1014, Condition C	
Mechanical Shock	MIL-STD-883, Method 2002, Condition B	
Moisture Resistance	MIL-STD-883, Method 1004	
Moisture Sensitivity	J-STD-020, MSL 1	
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, Method 1010, Condition B	
Vibration	MIL-STD-883, Method 2007, Condition A	

# EC2725ETTTS-66.666M

### **MECHANICAL DIMENSIONS (all dimensions in millimeters)**



PIN	CONNECTION	
1	Tri-State	
2	Ground/Case Ground	
3	Output	
4	Supply Voltage	
	MARKEN IN	
LINE	MARKING	
LINE 1	MARKING ECLIPTEK	

#### Suggested Solder Pad Layout

All Dimensions in Millimeters

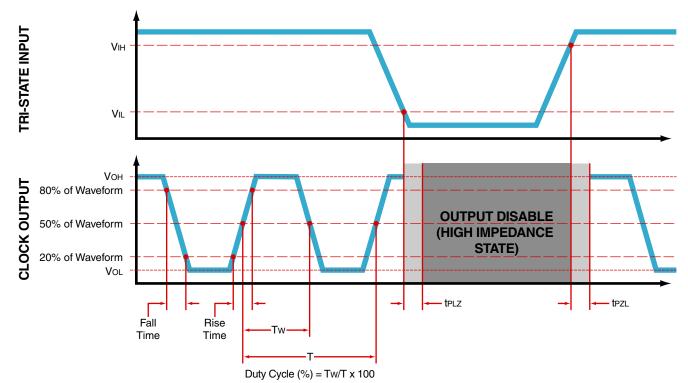


All Tolerances are ±0.1

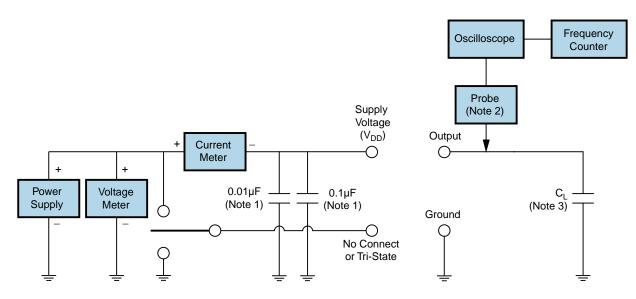


# EC2725ETTTS-66.666M





**Test Circuit for CMOS Output** 



Note 1: An external  $0.1\mu$ F low frequency tantalum bypass capacitor in parallel with a  $0.01\mu$ F high frequency ceramic bypass capacitor close to the package ground and V<sub>DD</sub> pin is required.

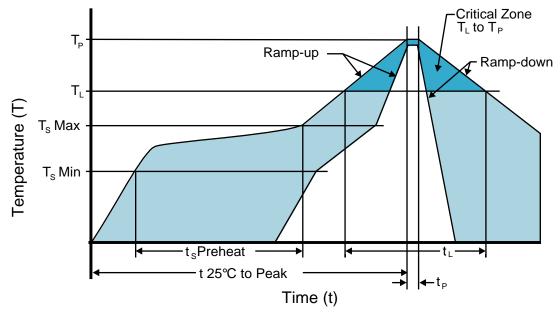
Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $\dot{C}_L$  includes sum of all probe and fixture capacitance.



## **Recommended Solder Reflow Methods**

EC2725ETTTS-66.666M



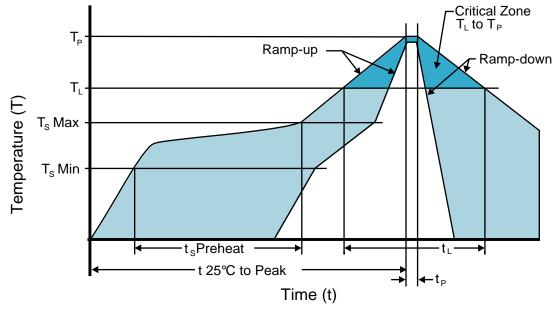
### **High Temperature Infrared/Convection**

<b>3</b> 1	
T <sub>s</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	150°C
<ul> <li>Temperature Typical (T<sub>s</sub> TYP)</li> </ul>	175°C
<ul> <li>Temperature Maximum (T<sub>s</sub> MAX)</li> </ul>	200°C
- Time (t <sub>s</sub> MIN)	60 - 180 Seconds
Ramp-up Rate (T⊾ to T <sub>P</sub> )	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T <sub>P</sub> )	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T <sub>P</sub> Target)	250°C +0/-5°C
Time within 5°C of actual peak (t <sub>p</sub> )	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



### **Recommended Solder Reflow Methods**

EC2725ETTTS-66.666M



### Low Temperature Infrared/Convection 240°C

T <sub>s</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	N/A
- Temperature Typical (T <sub>s</sub> TYP)	150°C
- Temperature Maximum (T <sub>s</sub> MAX)	N/A
- Time (t <sub>s</sub> MIN)	60 - 120 Seconds
Ramp-up Rate (T⊾ to T <sub>P</sub> )	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T <sub>P</sub> )	240°C Maximum
Target Peak Temperature (T <sub>P</sub> Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (t <sub>p</sub> )	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

#### Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

### **High Temperature Manual Soldering**

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)